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SEMICONDUCTOR DEVICE (54) MANUFACTURE OF

(57) Abstract:

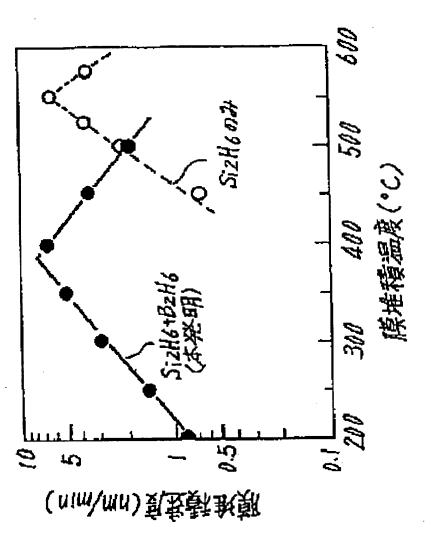
PURPOSE: To provide a method of characteristic and is just suitable for excellent step-portion covering including boron which ensures manufacturing a silicon film

manufacturing process under a low temperature condition.

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CONSTITUTION: An amorphous Si 400°C or lower using any one of disilane (Si2H6) or trisilane (Si3H6) film including boron which ensures characteristic can be formed. Using and dibolane (B2H6). Thereby, a Si source, extremely shallow junction reduced CVD method under a low the obtained Si film as a diffusion film is deposited by the pressuretemperature of 200 or higher and excellent step-portion covering may be formed. COPYRIGHT: (C)1993, JPO& Japio

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